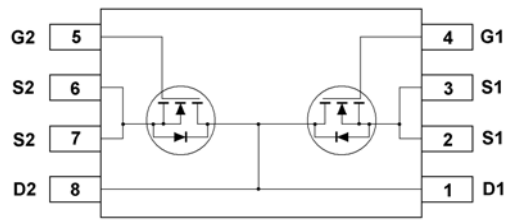


**Dual N-Channel Enhancement Mode MOSFET**

**Feature**

- 16V/6A,  $R_{DS(ON)} = 32m\Omega (MAX) @ V_{GS} = 4.5V$ .  
 $R_{DS(ON)} = 45m\Omega (MAX) @ V_{GS} = 2.5V$ .
- Super High dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handing capability.
- Lead free product is acquired.
- TSSOP-8 for Surface Mount Package.



**Applications**

- LI-ION Protection Circuit

**Absolute Maximum Ratings**

$T_A=25^{\circ}C$  Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	16	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Drain Current-Continuous	$I_D$	6	A

**Electrical Characteristics**

$T_A=25^{\circ}C$  Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0V, I_D=250\mu A$	16	-	-	V
Zero-Gate Voltage Drain Current	IDSS	$V_{DS}=6V, V_{GS}=0V$	-	-	1	$\mu A$
Gate Body Leakage Current, Forward	IGSSF	$V_{GS}=8V, V_{DS}=0V$	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	$V_{GS}=-8V, V_{DS}=0V$	-	-	-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.4	-	1.3	V
Static Drain-source	RDS(ON)	$V_{GS}=4.5V, I_D=6A$	-	-	32	$m\Omega$
On-Resistance		$V_{GS}=2.5V, I_D=5.2A$	-	-	45	$m\Omega$
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	VSD	$V_{GS}=0V, I_S=1.5A$			1.2	V

**Nanker Group**

**Headquarters:**

Tel: 0756-8128088 Fax: 0756-8889513  
E-mail: [info@nanker.com](mailto:info@nanker.com)

**Shenzhen Sales Office:**

Tel: 0755-86022782, 86022783, 86022910 Fax: 0755-86022774  
Website: [www.nanker.com](http://www.nanker.com)